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## VS-ST780CL

RoHS

COMPLIANT

**Vishay Semiconductors** 

## Phase Control Thyristors (Hockey PUK Version), 1350 A



B-PUK (TO-200AC)

PRIMARY CHARACTERISTICS								
I <sub>T(AV)</sub> 1350 A								
V <sub>DRM</sub> /V <sub>RRM</sub>	400 V, 600 V							
V <sub>TM</sub>	1.31 V							
I <sub>GT</sub>	100 mA							
TJ	-40 °C to +125 °C							
Package	B-PUK (TO-200AC)							
Circuit configuration	Single SCR							

### FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC)
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
1		1350	А				
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C				
I		2700	А				
I <sub>T</sub> (RMS)	T <sub>hs</sub>	25	°C				
1	50 Hz	24 400	A				
I <sub>TSM</sub>	60 Hz	25 600	A				
l <sup>2</sup> t	50 Hz	2986	kA <sup>2</sup> s				
14	60 Hz	2726	KA-S				
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 600	V				
t <sub>q</sub>	Typical	150	μs				
TJ		-40 to 125	C°				

### ELECTRICAL SPECIFICATIONS

VOLTAGE R	ATINGS			
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT T <sub>J</sub> = T <sub>J</sub> MAXIMUM mA
VS-ST780CL	04	400	500	80
V3-31780CL	06	600	700	00

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ABSOLUTE MAXIMUM RATINGS	SYMBOL		TEST CON		VALUES	UNITS	
	STINDUL	1000				A	
Maximum average on-state current at heatsink temperature	I <sub>T(AV)</sub>		180° conduction, half sine wave double side (single side) cooled		1350 (500)	°C	
					55 (85)	-C	
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	2700		
		t = 10 ms	No voltage		24 400		
Maximum peak, one-cycle	l	t = 8.3 ms	reapplied		25 600	А	
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RBM</sub>		20 550		
		t = 8.3 ms	reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	21 500		
		t = 10 ms	No voltage		2986	kA <sup>2</sup> s	
	l <sup>2</sup> t	t = 8.3 ms	reapplied		2726		
Maximum I <sup>2</sup> t for fusing		t = 10 ms	100 % V <sub>RBM</sub>		2112		
		t = 8.3 ms	reapplied		1928		
Maximum $I^2\sqrt{t}$ for fusing	l²√t	t = 0.1 to 10	ms, no voltage	reapplied	29 860	kA²√s	
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.80	v	
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	), T <sub>J</sub> = T <sub>J</sub> maxin	num	0.90	v	
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.14		
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.13	mΩ	
Maximum on-state voltage	V <sub>TM</sub>	$I_{pk} = 3600 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$			1.31	V	
Maximum holding current	Ι <sub>Η</sub>	т огоо			600		
Typical latching current	١L	I <sub>J</sub> = 25 °C,	anode supply 1	2 V resistive load	1000	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,  t_r \! \leq \! 1 \; \mu s$ $T_J = T_J$ maximum, anode voltage $\leq \! 80 \; \% \; V_{DRM}$	1000	A/μs
Typical delay time	t <sub>d</sub>	Gate current 1 A, dl <sub>g</sub> /dt = 1 A/ $\mu$ s V <sub>d</sub> = 0.67 % V <sub>DRM</sub> , T <sub>J</sub> = 25 °C	1.0	
Typical turn-off time	tq	$I_{TM}$ = 750 A, $T_J$ = $T_J$ maximum, dl/dt = 60 A/µs, $V_R$ = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ $t_p$ = 500 µs	150	μs

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/µs				
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	80	mA				



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TRIGGERING							
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES		
PANAMETEN	STMBOL	163	ST CONDITIONS	TYP.	MAX.	UNITS	
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum,	t <sub>p</sub> ≤5 ms	10	0.0	w	
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv	
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum,	t <sub>p</sub> ≤5 ms	3	.0	А	
Maximum peak positive gate voltage	+ V <sub>GM</sub>		t < 5 mg	20		v	
Maximum peak negative gate voltage	- V <sub>GM</sub>	ij = ij maximum,	$T_J = T_J$ maximum, $t_p \le 5$ ms			7 <sup>v</sup>	
		T <sub>J</sub> = -40 °C		200	-		
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Maximum required gate	100	200	mA	
		T <sub>J</sub> = 125 °C	trigger/current/voltage are the lowest value which will trigger	50	-		
		$T_J = -40 \ ^\circ C$	all units 12 V anode to cathode	2.5	-		
DC gate voltage required to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C	applied	1.8	3.0	V	
		T <sub>J</sub> = 125 °C		1.1	-		
DC gate current not to trigger	I <sub>GD</sub>		Maximum gate	10		mA	
DC gate voltage not to trigger	V <sub>GD</sub>	T <sub>J</sub> = T <sub>J</sub> maximum	current/voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode	0.:	25	V	

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to 125			
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150			
Maximum thermal registeres junction to besteink	D	DC operation single side cooled	0.073			
Maximum thermal resistance, junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.031	к/w		
Maximum thermal resistance, case to heatsink	D	DC operation single side cooled	0.011			
	R <sub>thC-hs</sub>	DC operation double side cooled	0.006			
Mounting force, ± 10 %			14 700 (1500)	N (kg)		
Approximate weight			255	g		
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-2	200AC)		

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAF	R CONDUCTION	TEST CONDITIONS	UNITS		
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS		
180°	0.009	0.009	0.006	0.006				
120°	0.011	0.011	0.011	0.011				
90°	0.014	0.014	0.015	0.015	$T_J = T_J maximum$	K/W		
60°	0.020	0.020	0.021	0.021				
30°	0.036	0.036	0.036	0.036				

Note

• The table above shows the increment of thermal resistance RthJ-hs when devices operate at different conduction angles than DC

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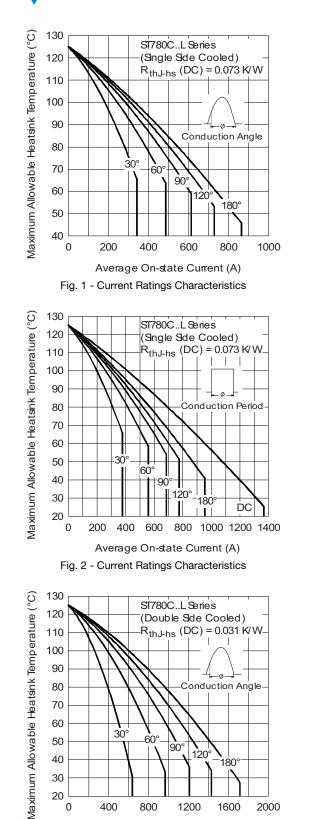
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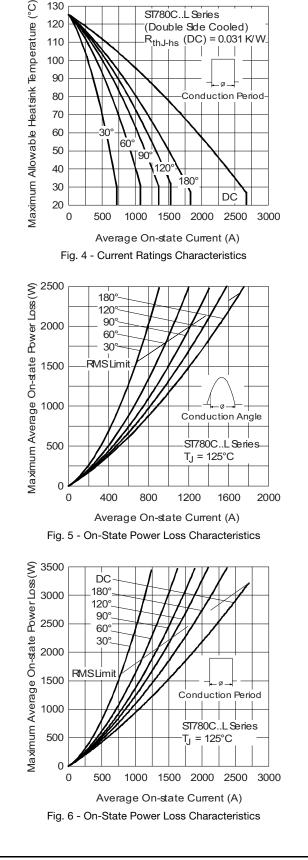


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Revision: 09-Jan-2025

0

400

800

Fig. 3 - Current Ratings Characteristics

Average On-state Current (A)

4

1600

1200

2000

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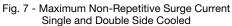


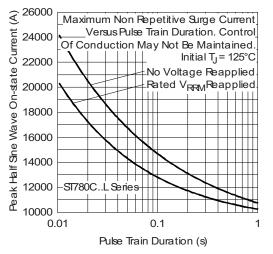
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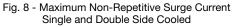
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Number Of Equal Amplitude Half Cycle Current Pulses (N)







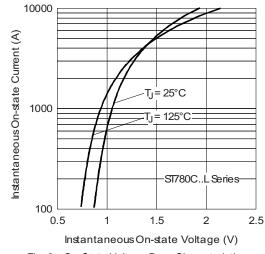
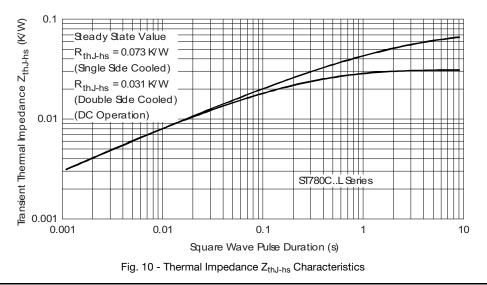


Fig. 9 - On-State Voltage Drop Characteristics



 Revision: 09-Jan-2025
 5
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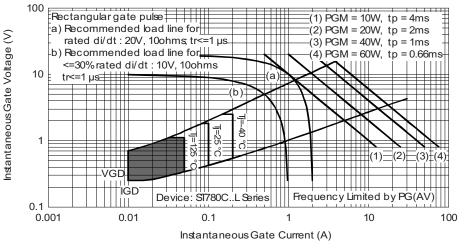


Fig. 11 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

Device code	VS-	ST	78	0	с	06	L	1	-
		(2)	(3)	4	(5)	6	$\overline{7}$	(8)	9
		$\bigcirc$	$\bigcirc$	$\bigcirc$	$\bigcirc$		$\bigcirc$	Ċ	Ċ
	<u> </u>	· Visł	nay Sem	nicondu	ctors pr	oduct			
	2 -	Thy	ristor						
	3 -	Ess	ential pa	art numl	oer				
	4 -	0 =	convert	er grade	Э				
	5 -	- C =	cerami	c PUK					
	6 -	· Volt	age coo	de x 100	$= V_{RRN}$	1 (see V	oltage F	Ratings	table)
	7 -	L=	PUK ca	se B-Pl	JK (TO-	200AC)			
	8 -	0 =	eyelet t	erminals	s (gate a	Ind auxi	iliary ca	thode u	nsolder
		1 =	fast-on	termina	ls (gate	and aux	kiliary ca	athode	unsolde
	9 -	- Crit	ical dV/	dt: • No	ne = 50	0 V/µs (	standar	d selec	tion)
				• L =	= 1000 V	//µs (sp	ecial sel	lection)	

LINKS TO RELATED DOCUMENTS					
Dimensions	http://www.vishay.com/doc?95076				

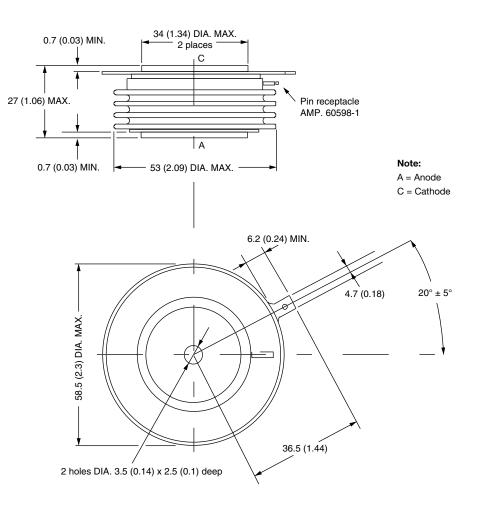
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## **B-PUK (TO-200AC)**

#### **DIMENSIONS** in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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1